Supporting Information

From optical pumping to electrical pumping: the threshold overestimation in metal halide perovskites

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Fig. S1. Fluence dependent PL at excitation wavelength of 420 nm. (a) PL spectra and (b) Integrated PL intensity and FWHM at different pump fluences.



Fig. S2. Fluence dependent PL at excitation wavelength of 440 nm. (a) PL spectra and (b) Integrated PL intensity and FWHM at different pump fluences.



Fig. S3. Fluence dependent PL at excitation wavelength of 460 nm. (a) PL spectra and (b) Integrated PL intensity and FWHM at different pump fluences.



Fig. S4. Fluence dependent PL at excitation wavelength of 480 nm. (a) PL spectra and (b) Integrated PL intensity and FWHM at different pump fluences.



Fig. S5. Absorption spectrum of the MAPbBr₃ film.



Fig. S6. Indication of fast carrier cooling process caused by two-photon up conversion process for MAPbBr₃ film. (a) Fluence dependent PL at excitation wavelength of 800 nm. (b) Comparison of ASE FWHM-ASE peak curves at different excitation photon energies.



Fig. S7. Fluence dependent PL at different excitation wavelengths of FAPbI₃ film. (a) 440 nm. (b) 500 nm. (c) 550 nm. (d) 600 nm. (e) 650 nm.



Fig. S8. (a) Absorption spectrum of the FAPbI₃ film. (b) Threshold carrier densities at different excitation wavelengths and the extrapolation to the near-to-band-edge photoexcitation wavelength (820 nm).